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We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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High Voltage PNP Silicon Plastic Power Transistors

These devices are designed for line operated audio output amplifier, switch—mode power supply drivers and other switching applications.

Features

- Popular TO-220 Plastic Package
- PNP Complements to the TIP47 thru TIP50 Series
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MJE5730 MJE5731 MJE5731A	V _{CEO}	300 350 375	Vdc
Collector-Base Voltage MJE5730 MJE5731 MJE5731A	V _{CB}	300 350 375	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous	I _C	1.0	Adc
Collector Current – Peak	I _{CM}	3.0	Adc
Base Current	Ι _Β	1.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	; = 25°C 40		W W/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Unclamped Inducting Load Energy (See Figure 10)	E	20	mJ
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

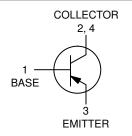
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

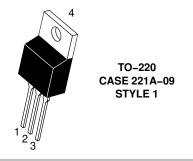


ON Semiconductor®

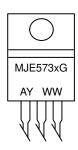
www.onsemi.com

1.0 AMPERE POWER TRANSISTORS PCP SILICON 300-350-400 VOLTS 50 WATTS





MARKING DIAGRAM



MJE573x = Device Code

x = 0, 1, or 1A

G = Pb-Free Package A = Assembly Location

Y = Year WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

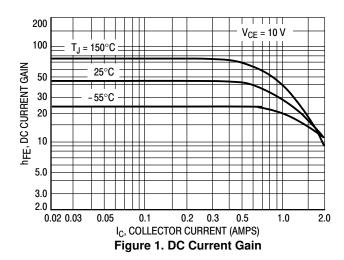
^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	1		•	•
Collector–Emitter Sustaining Voltage (Note 1)	V _{CEO(sus)}	300 350 375	- - -	Vdc
Collector Cutoff Current $ \begin{aligned} &(\text{V}_{\text{CE}} = 200 \text{ Vdc, I}_{\text{B}} = 0) \\ &\text{MJE5730} \end{aligned} \\ &(\text{V}_{\text{CE}} = 250 \text{ Vdc, I}_{\text{B}} = 0) \\ &\text{MJE5731} \end{aligned} \\ &(\text{V}_{\text{CE}} = 300 \text{ Vdc, I}_{\text{B}} = 0) \\ &\text{MJE5731A} \end{aligned}$	Iceo	- - -	1.0 1.0 1.0	mAdc
Collector Cutoff Current	l _{CES}	- - -	1.0 1.0 1.0	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	1.0	mAdc
ON CHARACTERISTICS (Note 1)	•		•	•
DC Current Gain ($I_C = 0.3$ Adc, $V_{CE} = 10$ Vdc) ($I_C = 1.0$ Adc, $V_{CE} = 10$ Vdc)	h _{FE}	30 10	150 -	_
Collector–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.2 Adc)	V _{CE(sat)}	-	1.0	Vdc
Base–Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 10 Vdc)	V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS	<u> </u>			
Current Gain – Bandwidth Product $(I_C = 0.2 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 2.0 \text{ MHz})$	f⊤	10	-	MHz
Small–Signal Current Gain (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	25	-	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



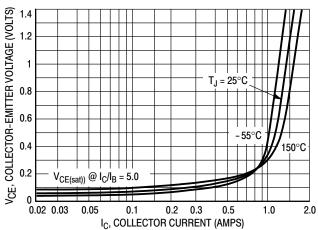


Figure 2. Collector-Emitter Saturation Voltage

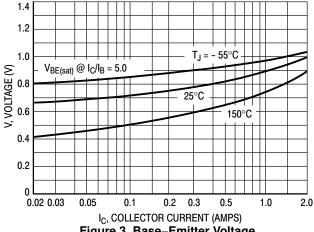


Figure 3. Base-Emitter Voltage

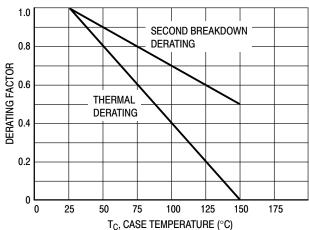


Figure 4. Normalized Power Derating

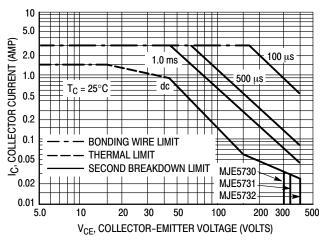


Figure 5. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150$ °C. $T_{J(pk)}$ may be calculated from the data in Figure 6. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

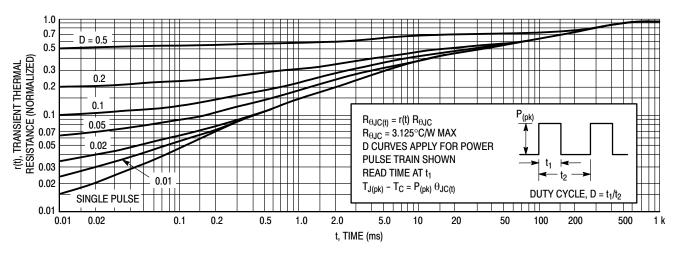


Figure 6. Thermal Response

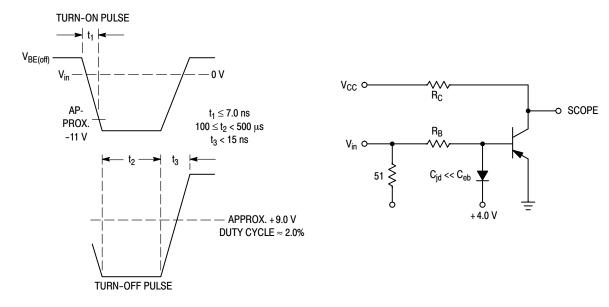


Figure 7. Switching Time Equivalent Circuit

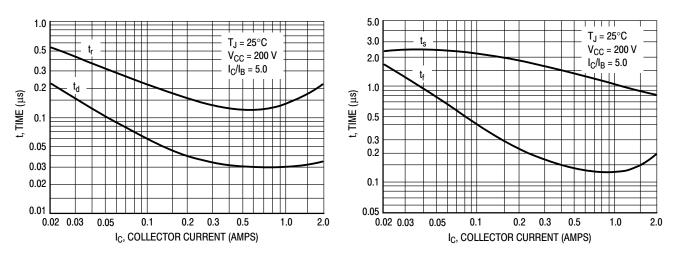
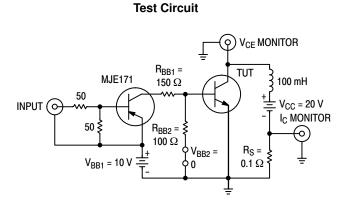


Figure 8. Turn-On Resistive Switching Times

Figure 9. Resistive Turn-Off Switching Times



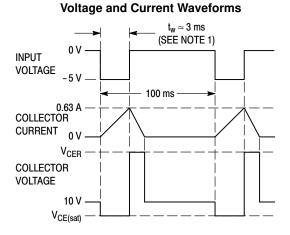


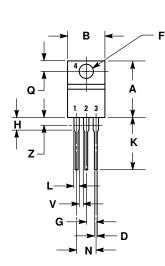
Figure 10. Inductive Load Switching

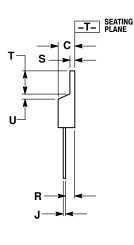
ORDERING INFORMATION

Device	Package	Shipping
MJE5730G	TO-220 (Pb-Free)	50 Units / Rail
MJE5731G	TO-220 (Pb-Free)	50 Units / Rail
MJE5731AG	TO-220 (Pb-Free)	50 Units / Rail

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
- T14:3M, 1902. CONTROLLING DIMENSION: INCH. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:

PIN 1. BASE

- COLLECTOR
- 3. **EMITTER**
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